Performance

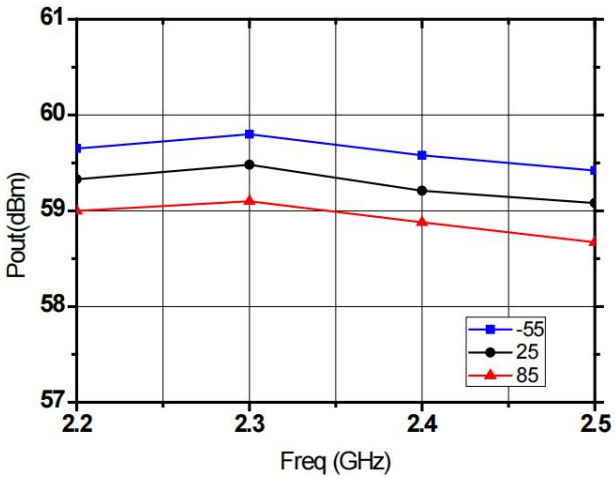
- Technology: 0.5um Power GaN HEMT
- Frequency: 2.2~2.5GHz
- Typical Pout : 59dBm
- Typical Gain: 12dB
- Typical PAE: 60%
- Bias: 48V/-3V
- Package: Metal Ceramic

Electrical Specifications (T_A=25℃,V_d=48V,PL=10us,D.C=2%,Vg=-3V,F: 2.2-2.5GHz)

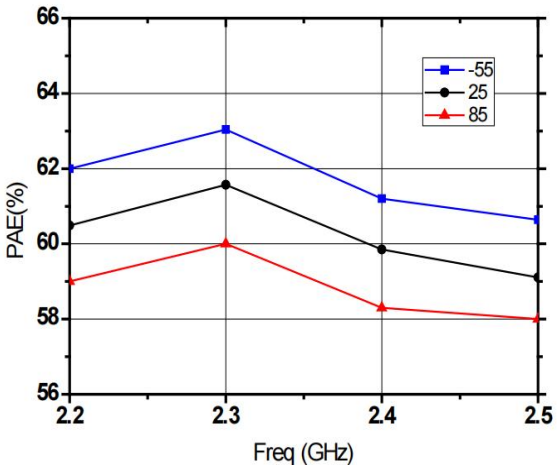
Symbol	Parameter	Min	Typical	Max	Unit
Pout	Output Power	-	59	-	dBm
Gp	Power Gain	-	12	-	dB
ηadd	Power Added Efficiency		60	-	%
Rth	Thermal Resistance	-	-	0.15	℃/W

Test Curves

Pout&Freq. @ Different Temp.



PAE&Freq. @ Different Temp.

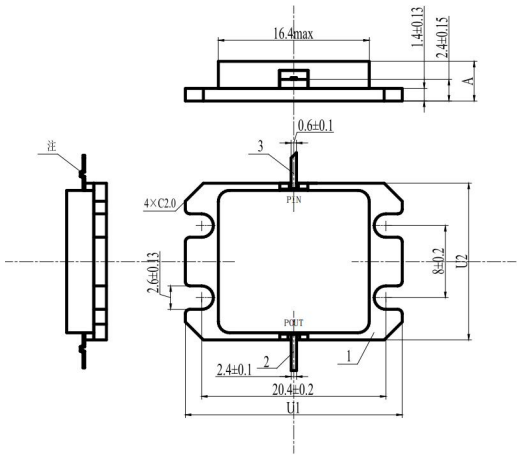


Absolute Max Ratings (T_A=25℃)

Symbol	Parameter	Value	Remark
Vd	Drain Voltage	60V	
Vg	Grid Voltage	-5V	
Tch	Channel Temperature	225℃	【1】
Tm	Mounting Temperature	300℃	1 min, N_2 Protection
Tstg	Storage Temperature	-55~175℃	
Tc	Operating Temperature	-55~85℃	

【1】Exceeding any one or combination of these limits may cause permanent damage.

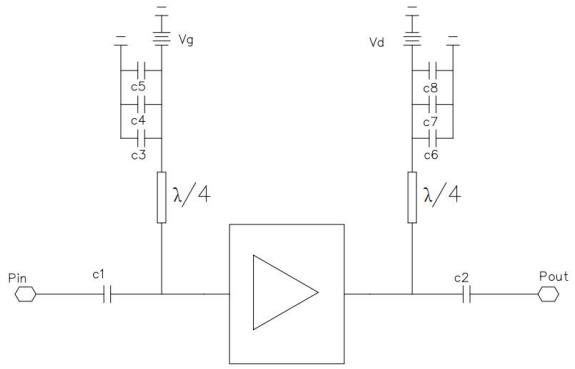
Outline Drawing



Dimension Symbol

Symbol	Value (unit: mm)		
	Min.	Typ.	Max.
U1	23.70	24.00	24.30
U2	17.20	17.40	17.60
A	-	4.50	6.00

Application Circuit



Capacitance	Value
C1、C2	20pF
C3、C6	100pF
C4、C7	1000pF
C5、C8	>10uF (Electrolytic capacitor or tantalum capacitor)

Note:

(1) This product is an internal matching tube, with input and output impedance values of 50 ohms;

(2) The power-on sequence shall be in strict accordance with the sequence of applying negative power first and then positive power. When power-off, the leakage voltage shall be reduced first and then the grid voltage shall be reduced;

(3) This product is a high-power device. Pay attention to heat dissipation during use. The higher the shell temperature is, the shorter the service life is. The service temperature should not be higher than 80 ℃;

(4) This product is an electrostatic sensitive device. It needs to pay attention to electrostatic protection during storage and use, and it needs to be grounded well during use.